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***SUBSTITUTE ABSTRACT***

## ABSTRACT OF THE DISCLOSURE

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A semiconductor device includes a convex semiconductor layer provided on a semiconductor substrate, a source region and a drain region provided in the convex semiconductor layer, and a gate electrode having a side-wall gate portion provided over a side surface of the convex semiconductor layer. The side-wall gate portion of the gate electrode is offset with respect to a part of the lower portion of the source region and a part of the lower portion of the drain region.

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